What is Claimed:

1. A method of packaging a semiconductor device including a plurality of elements, the method comprising the steps of:

applying an insulative material to at least a portion of the semiconductor device, the insulative material including insulative particles having a diameter smaller than a gap between adjacent conductors providing interconnection between the elements; and

curing the insulative material.

2. The method of claim 1 wherein said applying step includes applying the insulative material including silica particles and a polymer resin.

3. The method of claim 1 wherein said curing step includes exposing the insulative material to at least one of ultraviolet, visible, and infrared radiation.

4. The method of claim 1 wherein said curing step includes heating the insulative material and exposing the insulative material to at least one of ultraviolet, visible, and infrared radiation.

5. The method of claim 1 wherein the curing step includes applying a thermal process to the insulative material including a ramp up in temperature, a soak in temperature, and a ramp down in temperature.

6. The method of claim 1 wherein the applying step includes applying the insulative material to the device wherein the insulative particles occupy between 50 and 85 percent of the volume of the insulative material.

7. The method of claim 1 wherein said applying step includes applying the insulative material to the device wherein the insulative particles have a maximum diameter of 20 microns.

8. The method of claim 1 wherein said applying step includes applying the insulative material to the device wherein the insulative particles have a median diameter of approximately 4.5 microns.

9. The method of claim 1 wherein said applying step includes applying the insulative material to the device wherein the insulative particles have a mean diameter of approximately 4.1 microns.

10. The method of claim 1 wherein through said applying step the insulative particles disperse between adjacent ones of the conductors, thereby providing insulated separation between the ones of the conductors.

11. The method of claim 1 further comprising the step of:

heating the semiconductor device to a temperature of between 50 and 125°C before the applying step.

12. The method of claim 1 further comprising the step of:

heating the semiconductor device to a temperature of between 80 and 100°C before the applying step.

13. The method of claim 1 further comprising the step of:

heating the insulative material to a temperature between 35 and 85 °C before the applying step.

14. The method of claim 1 further comprising the step of:

heating the insulative material to a temperature between 50 and 70 °C before the applying step.

15. The method of claim 1 further comprising the step of:

encapsulating the semiconductor device.

16. The method of claim 15 wherein said encapsulating step includes encapsulating the semiconductor device with an overmold encapsulant.

17. The method of claim 15 wherein said encapsulating step includes encapsulating the semiconductor device with a globtop encapsulant.

18. The method of claim 1 wherein said applying step includes applying the insulative material to a semiconductor element positioned at a substantially central portion of the semiconductor device, such that the insulative material disperses from the semiconductor element onto the plurality of conductors.

19. The method of claim 1 further comprising the step of:

drawing at least one of the insulative particles between adjacent ones of the conductors, thereby separating the adjacent ones of the conductors, the adjacent ones of the conductors previously being in contact with one another before said step of drawing.

20. The method of claim 1 further comprising the step of:

providing a period of time between 2 and 50 seconds for the insulative material to flow prior to said curing step, the period of time being selected based on at least one of a size of the semiconductor device, a temperature of the semiconductor device, a temperature of the insulative material during said step of applying, and a density of the conductors providing interconnection between the elements.

21. The method of claim 1 further comprising the step of:

providing a period of time between 7 and 25 seconds for the insulative material to flow prior to said curing step, the period of time being selected based on at least one of a size of the semiconductor device, a temperature of the semiconductor device, a temperature of the insulative

material during said step of applying, and a density of the conductors providing interconnection between the elements.

22. A semiconductor device comprising:

a plurality of semiconductor elements;

a plurality of conductors providing interconnection between said plurality of semiconductor elements; and

an insulative material including insulative particles having a diameter smaller than a gap between adjacent ones of said plurality of conductors, said insulative material covering at least a portion of said plurality of conductors.

23. The semiconductor device of claim 22 wherein said insulative material includes a polymer resin, and said insulative particles are silica particles.

24. The semiconductor device of claim 22 wherein said insulative material is at least partially cured by at least one of ultraviolet, visible, and infrared radiation.

25. The semiconductor device of claim 22 wherein said insulative particles occupy between 50 and 85 percent of the volume of said insulative material.

26. The semiconductor device of claim 22 wherein said insulative particles have a maximum diameter of 20 microns.

27. The semiconductor device of claim 22 wherein said insulative particles have a median diameter of approximately 4.5 microns.

28. The semiconductor device of claim 22 wherein said insulative particles have a mean diameter of approximately 4.1 microns.

29. The semiconductor device of claim 22 wherein said insulative particles provide insulated separation between at least two of said plurality of conductors.

30. The semiconductor device of claim 22 further comprising an encapsulation layer encapsulating said plurality of semiconductor elements, said plurality of conductors, and said insulative material.

31. The semiconductor device of claim 30 wherein said encapsulation layer includes an overmold encapsulant.

32. The semiconductor device of claim 30 wherein said encapsulation layer includes a globtop encapsulant.

33. The semiconductor device of claim 30 wherein each of said plurality of conductors have a length at least 250 times greater than a diameter of the respective conductor.

34. The semiconductor device of claim 24 wherein a period of time between 2 and 50 seconds is provided for said insulative material to flow prior to curing said insulative material, the period of time being selected based on at least one of a size of said semiconductor device, a temperature of said semiconductor device, a temperature of said insulative material during application to said portion of said plurality of conductors, and a density of said conductors providing interconnection between said elements.

35. The semiconductor device of claim 24 wherein a period of time between 7 and 25 seconds is provided for said insulative material to flow prior to curing said insulative material, the period of time being selected based on at least one of a size of said semiconductor device, a temperature of said semiconductor device, a temperature of said insulative material during application to said portion of said plurality of conductors, and a density of said conductors providing interconnection between said elements.